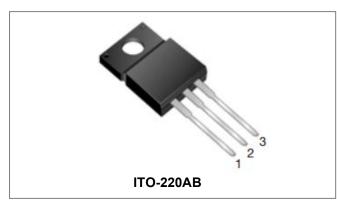






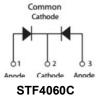
STF4060C(R) SCHOTTKY RECTIFIER

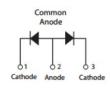


Features

- 150 °C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram





STF4060CR

Applications

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=100°C, rectangular wave form	20(Per Leg) 40(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse, Tc=25°C	240	А

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R _θ JC	DC operation	5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

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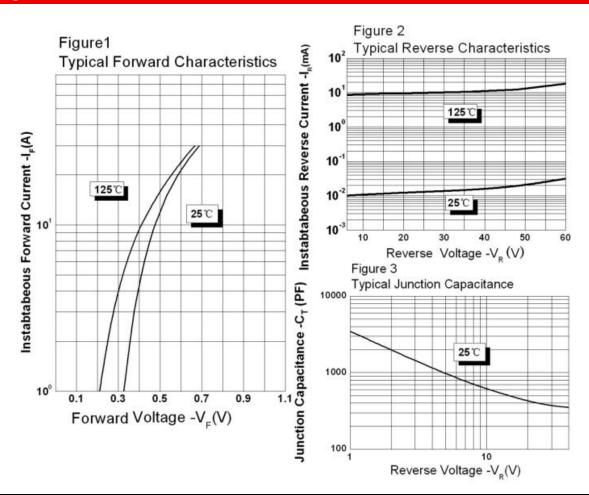


Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)* V _{F1} @ 10A, Pulse, T _J = 25°C		@ 10A, Pulse, T _J = 25°C	0.48	-	V
		@ 20A, Pulse, T _J = 25°C	0.59	0.62	V
	V _{F2}	@ 10A, Pulse, T _J = 25°C	0.41	-	V
		@ 20A, Pulse, T _J =125℃	0.55	0.57	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25 ℃	0.031	6	mA
	I _{R2}	$@V_R = \text{rated } V_{R,} T_J = 125^{\circ}C$	18.4	190	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	949	-	pF
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T _A = 25 °C)		Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	
·	V _{ISO}	Clip mounting, the epoxy body is inside the heatsink.	-	3500	V
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

^{*} Pulse width < 300 µs, duty cycle < 2%

Ratings and Characteristics Curves



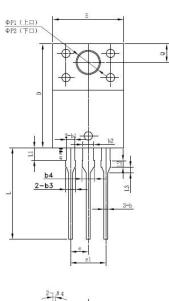
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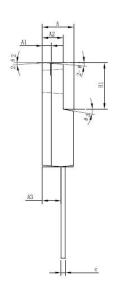






Mechanical Dimensions ITO-220AB

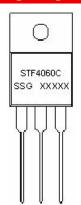


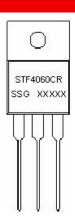




SYMBOL	Millimeters			
STWIBUL	MIN.	TYP.	MAX.	
Α	4.30	4.50	4.70	
A1	1.10	1.30	1.50	
A2	2.80	3.00	3.20	
A3	2.50	2.70	2.90	
b	0.50	0.60	0.75	
b1	1.10	1.20	1.35	
b2	1.50	1.60	1.75	
b3	1.20	1.30	1.45	
b4	1.60	1.70	1.85	
С	0.50	0.60	0.75	
D	14.80	15.00	15.20	
E	9.96	10.16	10.36	
e		2.55		
e1		5.10		
H1	6.50	6.70	6.90	
L	12.70	13.20	13.70	
L1	1.60	1.80	2.00	
L2	0.80	1.00	1.20	
L3	0.60	0.80	1.00	
ΦΡ1(├ □)	3.30	3.50	3.70	
ΦP2 (下口)	2.99	3.19	3.39	
Q	2.50	2.70	2.90	
Θ1		5°		
Θ2		4°		
Θ3		10°		
Θ4		5°		
Θ5		5°		

Marking Diagram





Where XXXXX is YYWWL

 ST
 = Device Type

 F
 = Package type

 40
 = Forward Current (40A)

 60
 = Reverse Voltage (60V)

 C(R)
 = Configuration

 SSG
 = SSG

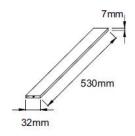
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Tube Specification



Ordering Information

Device	Package	Shipping
STF4060C(R)	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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